BLS7G3135L-350P; BLS7G3135LS-350P

LDMOS S-band radar power transistor

Rev. 3 — 29 October 2013 Product data sheet

1. Product profile

1.1 General description

350 W LDMOS power transistor intended for radar applications in the 3.1 GHz to 3.5 GHz range.

Table 1. Typical performance

Typical RF performance at T_{case} = 25 °C; t_p = 300 µs; δ = 10 %; I_{Dq} = 200 mA; in a class-AB production test circuit.

Test signal	f	V_{DS}	P_L	G_p	η_D	t_r	t_f
	(GHz)	(V)	(W)	(dB)	(%)	(ns)	(ns)
pulsed RF	3.1	32	350	12	43	5	5
	3.3	32	350	12	43	5	5
	3.5	32	350	10	39	5	5

1.2 Features and benefits

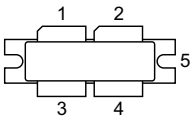
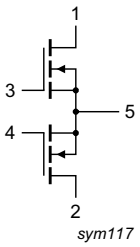
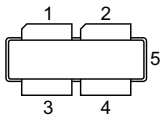
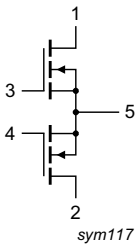
- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (3.1 GHz to 3.5 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

1.3 Applications

- S-Band power amplifiers for radar applications in the 3.1 GHz to 3.5 GHz frequency range

2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLS7G3135L-350P (SOT539A)				
1	drain1			
2	drain2			
3	gate1			
4	gate2			
5	source	[1]		
BLS7G3135LS-350P (SOT539B)				
1	drain1			
2	drain2			
3	gate1			
4	gate2			
5	source	[1]		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLS73135L-350P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A
BLS73135LS-350P	-	earless flanged balanced ceramic package; 4 leads	SOT539B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter		Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		–0.5	+11	V
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature	[1]	-	225	°C

[1] Continuous use at maximum temperature will affect the reliability. For details refer to the on-line MTF calculator.

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
$Z_{th(j-mb)}$	transient thermal impedance from junction to mounting base	T_{case} = 85 °C; P_L = 350 W		
		t_p = 300 μs; δ = 10 %	0.1	K/W
		t_p = 100 μs; δ = 20 %	0.09	K/W
		t_p = 100 μs; δ = 10 %	0.07	K/W
		t_p = 200 μs; δ = 10 %	0.09	K/W

6. Characteristics

Table 6. DC characteristics

T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	V_{GS} = 0 V; I_D = 2.2 mA	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	V_{DS} = 10 V; I_D = 220 mA	1.5	1.9	2.3	V
I_{DSS}	drain leakage current	V_{GS} = 0 V; V_{DS} = 28 V	-	-	2.8	μA
I_{DSX}	drain cut-off current	V_{GS} = $V_{GS(th)}$ + 3.75 V; V_{DS} = 10 V	-	39	-	A
I_{GSS}	gate leakage current	V_{GS} = 11 V; V_{DS} = 0 V	-	-	280	nA
g_{fs}	forward transconductance	V_{DS} = 10 V; I_D = 11 A	-	16.2	-	S
$R_{DS(on)}$	drain-source on-state resistance	V_{GS} = $V_{GS(th)}$ + 3.75 V; I_D = 7.7 A	-	0.065	-	Ω

Table 7. RF characteristics

Test signal: pulsed RF; t_p = 300 μs; δ = 10 %; RF performance at V_{DS} = 32 V; I_{Dq} = 200 mA; T_{case} = 25 °C; unless otherwise specified, in a class-AB production circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
At frequency of 3.1 GHz						
G_p	power gain	P_L = 350 W	10.5	12	-	dB
RL_{in}	input return loss	P_L = 350 W	-	−6	-	dB
η_D	drain efficiency	P_L = 350 W	38	43	-	%
$P_{droop(pulse)}$	pulse droop power	P_L = 350 W	-	0.2	0.3	dB
t_r	rise time	P_L = 350 W	-	5	50	ns
t_f	fall time	P_L = 350 W	-	5	50	ns
At frequency of 3.3 GHz						
G_p	power gain	P_L = 350 W	10.5	12	-	dB
RL_{in}	input return loss	P_L = 350 W	-	−6	-	dB
η_D	drain efficiency	P_L = 350 W	38	43	-	%
$P_{droop(pulse)}$	pulse droop power	P_L = 350 W	-	0.2	0.3	dB
t_r	rise time	P_L = 350 W	-	5	50	ns
t_f	fall time	P_L = 350 W	-	5	50	ns
At frequency of 3.5 GHz						
G_p	power gain	P_L = 320 W	8.5	10	-	dB
RL_{in}	input return loss	P_L = 320 W	-	−9	-	dB
η_D	drain efficiency	P_L = 320 W	35	39	-	%
$P_{droop(pulse)}$	pulse droop power	P_L = 320 W	-	0.2	0.3	dB
t_r	rise time	P_L = 320 W	-	5	50	ns
t_f	fall time	P_L = 320 W	-	5	50	ns

7. Application information

7.1 Ruggedness in class-AB operation

The BLS7G3135L-350P and the BLS7G3135LS-350P are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 200 mA; P_L = 350 W; t_p = 300 μs; δ = 10 %

7.2 Impedance information

Table 8. Typical impedance

Measured load-pull data. Typical values unless otherwise specified.

f	Z_S[1]	Z_L[1]
(GHz)	(Ω)	(Ω)
3.1	1.8 – 7.2j	3.6 – 6.3j
3.2	1.6 – 7.1j	4.4 – 6.7j
3.3	2.2 – 8.2j	4.8 – 5.8j
3.4	3.1 – 9.7j	5.7 – 6.2j
3.5	3.6 – 11.6j	6.5 – 4.6j

[1] Impedances are taken at a single half of the push-pull transistor.

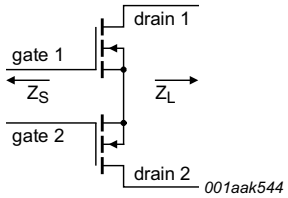
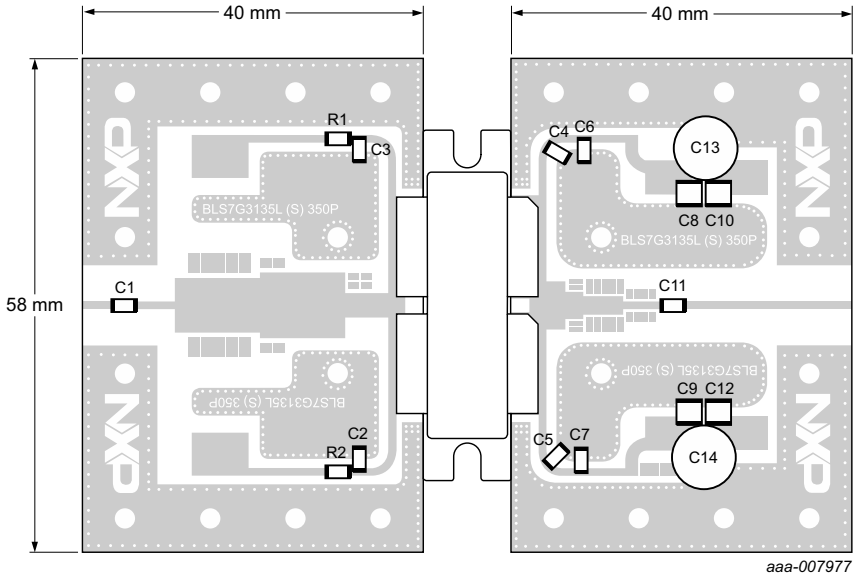


Fig 1. Definition of transistor impedance

7.3 Test circuit information



Printed-Circuit Board (PCB): Rogers 3006; ε_r = 6.15; thickness = 0.64 mm; thickness copper plating = 35 μm

See Table 9 for a list of components.

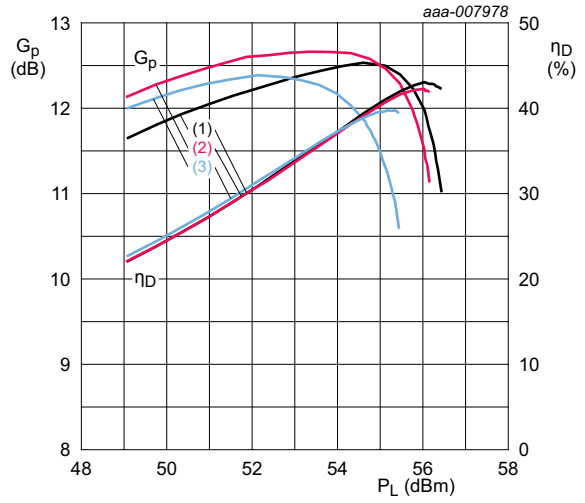
Fig 2. Test circuit layout

Table 9. List of components

For test circuit see Figure 2.

Component	Description	Value	Remarks
C1, C2, C3	multilayer ceramic chip capacitor	8.2 pF	ATC100A
C4, C5, C11	multilayer ceramic chip capacitor	15 pF	ATC800B
C6, C7	multilayer ceramic chip capacitor	100 pF	ATC800A
C8, C9	multilayer ceramic chip capacitor	1 μF, 50 V	TDK
C10, C12	multilayer ceramic chip capacitor	10 μF, 50 V	TDK
C13, C14	electrolytic capacitor	220 μF, 63 V	
R1, R2	SMD resistor	10 Ω	

7.4 Graphical data



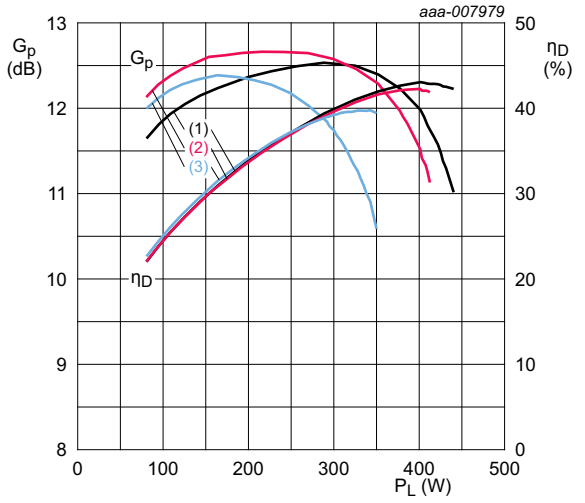
V_{DS} = 32 V; I_{Dq} = 200 mA.

(1) f = 3100 MHz

(2) f = 3300 MHz

(3) f = 3500 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values



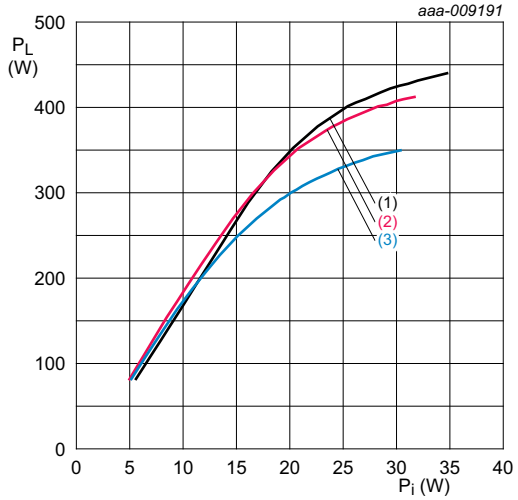
V_{DS} = 32 V; I_{Dq} = 200 mA.

(1) f = 3100 MHz

(2) f = 3300 MHz

(3) f = 3500 MHz

Fig 4. Power gain and drain efficiency as function of output power; typical values



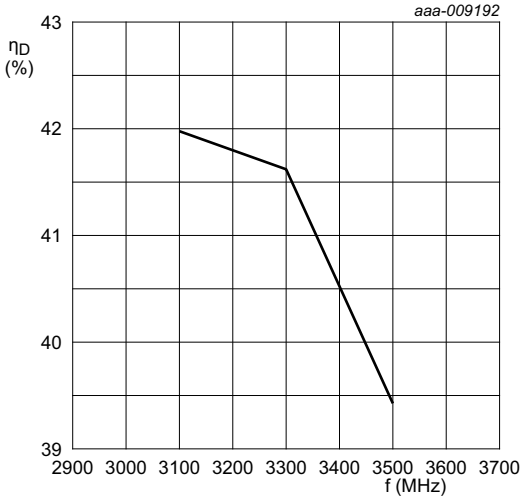
V_{DS} = 32 V; I_{Dq} = 200 mA; t_p =300 μs; δ = 10 %.

(1) f = 3100 MHz

(2) f = 3300 MHz

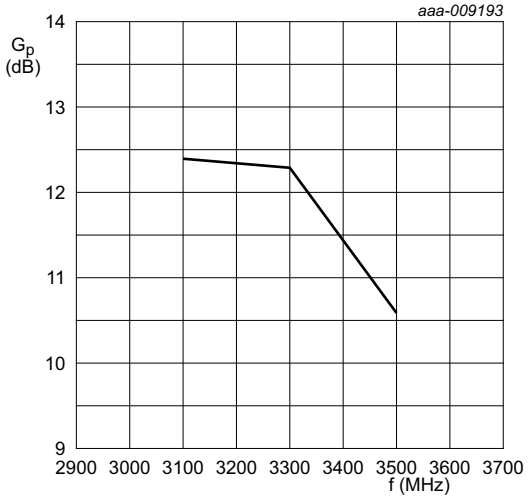
(3) f = 3500 MHz

Fig 5. Output power as a function of input power; typical values



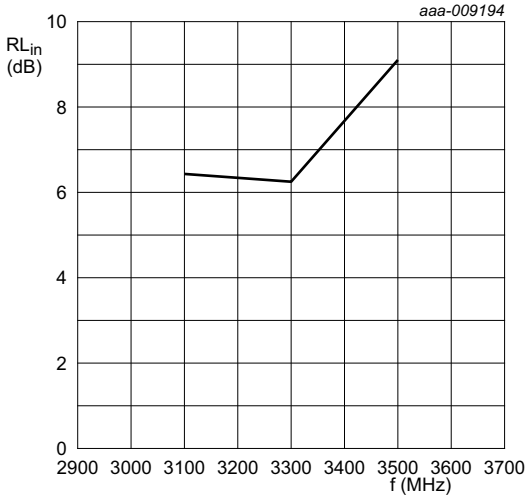
V_{DS} = 32 V; I_{Dq} = 200 mA; t_p = 300 μs; δ = 10 %; P_L = 350 W.

Fig 6. Drain efficiency as a function of frequency; typical values



V_{DS} = 32 V; I_{Dq} = 200 mA; t_p = 300 μs; δ = 10 %; P_L = 350 W.

Fig 7. Power gain as a function of frequency; typical values

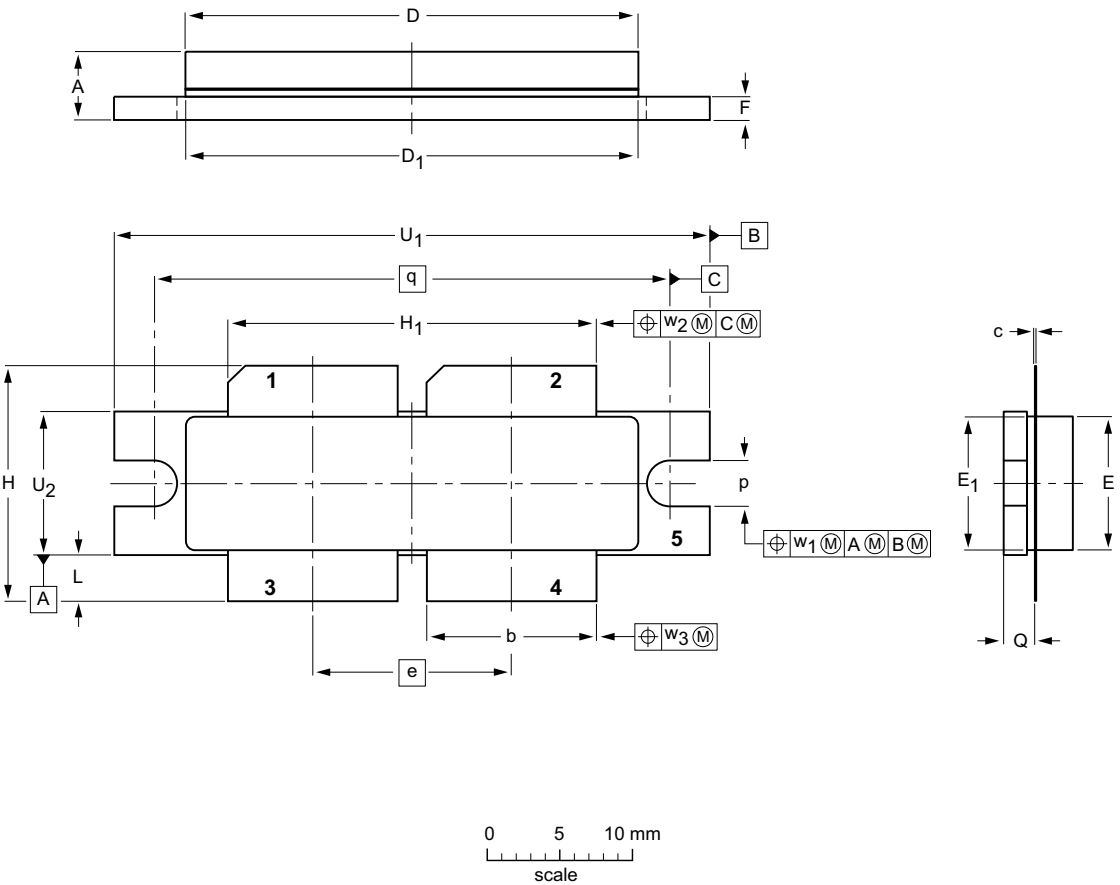


V_{DS} = 32 V; I_{Dq} = 200 mA; t_p = 300 μs; δ = 10 %; P_L = 350 W.

Fig 8. Input return loss as a function of frequency; typical values

8. Package outline

Flanged balanced ceramic package; 2 mounting holes; 4 leads **SOT539A**



DIMENSIONS (millimetre dimensions are derived from the original inch dimensions)

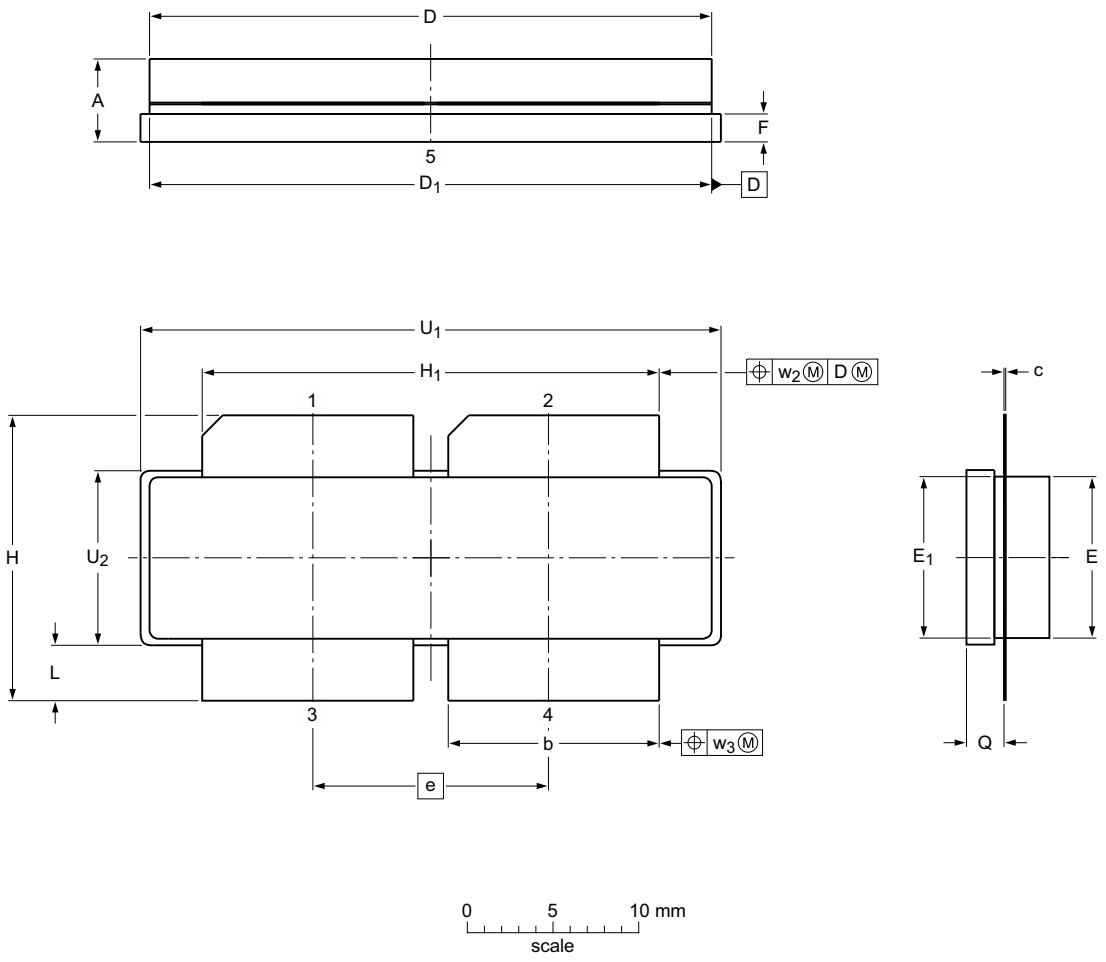
UNIT	A	b	c	D	D_1	e	E	E_1	F	H	H_1	L	p	Q	q	U_1	U_2	w_1	w_2	w_3
mm	4.7 4.2	11.81 11.56	0.18 0.10	31.55 30.94	31.52 30.96	13.72	9.50 9.30	9.53 9.27	1.75 1.50	17.12 16.10	25.53 25.27	3.48 2.97	3.30 3.05	2.26 2.01	35.56	41.28 41.02	10.29 10.03	0.25	0.51	0.25
inches	0.185 0.165	0.465 0.455	0.007 0.004	1.242 1.218	1.241 1.219	0.540	0.374 0.366	0.375 0.365	0.069 0.059	0.674 0.634	1.005 0.995	0.137 0.117	0.130 0.120	0.089 0.079	1.400	1.625 1.615	0.405 0.395	0.010	0.020	0.010

Note
1. millimeter dimensions are derived from the original inch dimensions.
2. recommended screw pitch dimension of 1.52 inch (38.6 mm) based on M3 screw.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT539A						~~10-02-02~~ 12-05-02

Fig 9. Package outline SOT539A

Earless flanged balanced ceramic package; 4 leads **SOT539B**



Dimensions

Unit[1]		A	b	c	D	D_1	E	E_1	e	F	H	H_1	L	Q	U_1	U_2	w_2	w_3
mm	max	4.7	11.81	0.18	31.55	31.52	9.5	9.53		1.75	17.12	25.53	3.48	2.26	32.39	10.29		
	nom								13.72								0.25	0.25
	min	4.2	11.56	0.10	30.94	30.96	9.3	9.27		1.50	16.10	25.27	2.97	2.01	32.13	10.03		
inches	max	0.185	0.465	0.007	1.242	1.241	0.374	0.375		0.069	0.674	1.005	0.137	0.089	1.275	0.405		
	nom								0.54								0.01	0.01
	min	0.165	0.455	0.004	1.218	1.219	0.366	0.365		0.059	0.634	0.995	0.117	0.079	1.265	0.395		

Note
1. millimeter dimensions are derived from the original inch dimensions.

sot539b_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT539B						~~12-05-02~~ 13-05-24

Fig 10. Package outline SOT539B

9. Handling information

CAUTION

This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal Oxide Semiconductor
S-Band	Short wave band
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLS73135L-350P_7G3135LS-350P v.3	20131029	Product data sheet	-	BLS73135L-350P_ 7G3135LS-350P v.2
Modifications	• Table 1 on page 1: table updated • Table 6 on page 3: table updated • Table 7 on page 4: table updated • Section 7.4 on page 6: 4 graphs added			
BLS73135L-350P_7G3135LS-350P v.2	20130801	Objective data sheet	-	BLS73135L-350P_ 7G3135LS-350P v.1
BLS73135L-350P_7G3135LS-350P v.1	20121012	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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14. Contents

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